

Form PTO-1449 (Modified)		Atty Docket No.: P18611		Serial No.: Unknown 16/805,880			
List of Patents and Publications Statement (Use several sheets if necessary) lgwe ANYA AU 2825				Applicant: Uday Shah et al.			
				Filing Date: March 22, 2004			
REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS				
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate	
JA	AA	6,063,698	Tseng et al.	438	585		
	AB	6,184,072 B1	Kaushik et al.	438	197		
	AC	6,420,279 B1	Ono et al.	438	785		
	AD	6,475,874 B2	Xiang et al.	438	396		
	AE	6,514,828 B2	Ahn et al.	438	240		
	AF	6,544,906 B2	Rotondaro et al.	438	785		
	AG	6,617,209 B1	Chau et al.	438	240		
	AH	6,617,210 B1	Chau et al.	438	240		
	AI	6,620,713 B2	Arghavani et al.	438	585		
	AJ	6,689,675 B1	Parker et al.	438	585		
	AK	6,696,327 B1	Brask et al.	438	197		
	AL	6,696,345 B2	Chau et al.	438	387		
	AM	US2002/0197790 A1	Kizilyalli et al.	438	240		
	AN	US2003/0032303 A1	Yu et al.	438	770		
	AO	US2003/0045080 A1	Visokay et al.	438	591		
	AP						
	FOREIGN PATENT DOCUMENTS						
		Document No.	Date	Country	Class	Sub-Class	Translation
	AQ						
	AR						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
JA	AS	Polishchuk et al., "Dual Workfunction CMOS Gate Technology Based on Metal Interdiffusion", www.eesc.berkeley.edu , 1 page					
	AT	Doug Barlage et al., "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages					
	AU	Lu et al., "Dual-Metal Gate Technology for Deep-Submicron CMOS Devices", dated April 29, 2003, 1 page					
	AV	Schwantes et al., "Performance Improvement of Metal Gate CMOS Technologies with Gigabit Feature Sizes", Technical University of Hamburg-Harburg, 5 pages					
	AW	Brask et al., "A Method for Making a Semiconductor Device Having a Metal Gate Electrode," Serial No. 10/704,497, Filed November 6, 2003					
	AX	Brask et al., "A Method for Etching a Thin Metal Layer", Serial No. 10/704,498, Filed November 6, 2003					
JA	AY	Brask et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode that is Formed on an Annealed High-K Gate Dielectric Layer", Serial No. 10/742,678, Filed December 19, 2003					
	AZ						
Examiner A. J. ...			Date Considered 9/16/04				
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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